

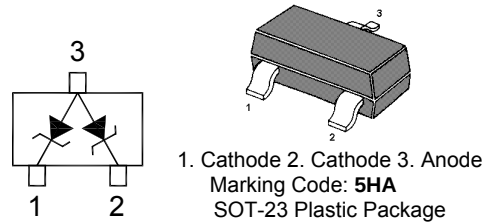
ESD05CA

Silicon Epitaxial Planar Diodes

TVS diode array for ESD protection in portable electronics

Features

- Protects one bidirectional line or two unidirectional lines
- Low clamping voltage
- Low leakage current



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Stand-Off Voltage	V_{RWM}	5	V
Peak Pulse Current ($t_p = 8/20 \mu\text{s}$)	I_{PP}	24	A
Peak Pulse Power ($t_p = 8/20 \mu\text{s}$)	P_{PK}	350	W
Operation Temperature Range	T_j	- 55 to + 150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

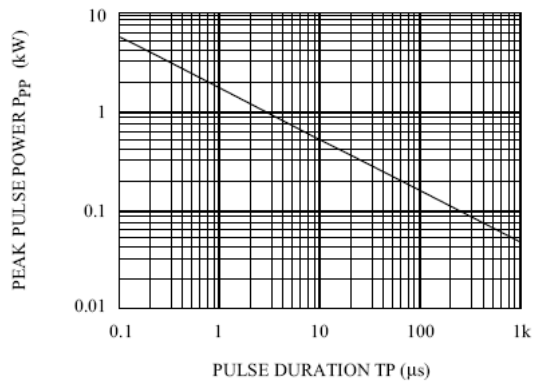
Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 1 \text{ mA}$	$V_{(BR)R}$	6	-	V
Reverse Current at $V_R = 5 \text{ V}$	I_R	-	20	μA
Clamping Voltage at $I_{PP} = 24 \text{ A}$, $t_p = 8/20 \mu\text{s}$	V_C	-	14.5	V
Junction Capacitance at $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$ (Pin 1 to 3 and Pin 2 to 3)	C_J	-	400	pF

TOP DYNAMIC

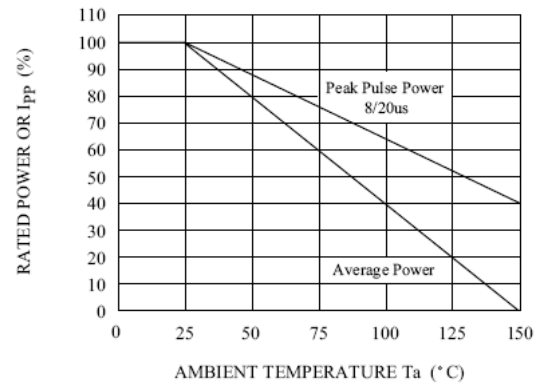


Dated : 16/09/2012 Rev:01

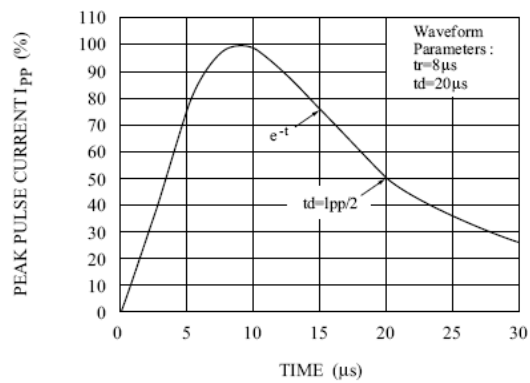
NON-REPETITIVE PEAK PULSE POWER VS. PULSE TIME



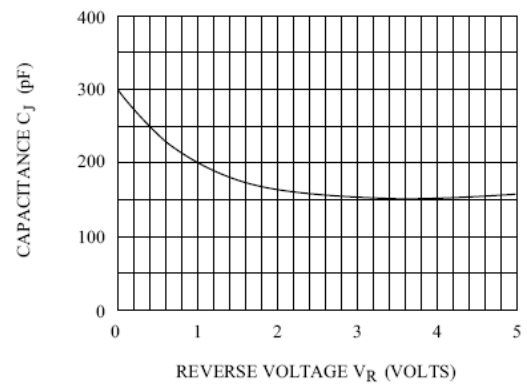
POWER DERATION CURVE



PULSE WAVEFORM



$C_J - V_R$



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